



## Information about product quality of device type BZA862A

Quality and reliability data provided by NXP Semiconductors is intended to be a non-binding estimate of product performance only. It does not imply that any performance levels reflected in such data can be met if the product is operated outside the conditions expressly stated in the latest published data sheet for a device or in your application.

Quick reference:

- Device Type: BZA862A
- Ordering Information (12NCs): 9340 560 43115
- Qualification Grade: automotive
- Package: SOT353
- Waferfab: NXP DHAM
- Assembly: NXP APM
- ESD HBM: > 8000 V
- ESD MM: > 400 V
- Calculated Failure Rate: 0.73 FIT
- MTBF/MTTF: 1374267530 hours

Explanation:

Automotive qualified products are in accordance with the AEC Q101.

Electrostatic Discharge (ESD) tests are performed as described in the AEC Q101 with each 3 positive and 3 negative pulses for each stress voltage level.

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, AEC Q101 Test # 5). The parameters for calculation of FIT and MTBF/MTTF are as follows: Confidence level 60%, junction temperature derated to 55 °C, activation energy 0.7 eV, test time 168 - 1000 hrs.

For discrete semiconductor devices the Mean Time Between Failure (MTBF) is replaced by the Mean Time To Failure (MTTF) acronym. MTTF is calculated from the Intrinsic Failure Rate.